

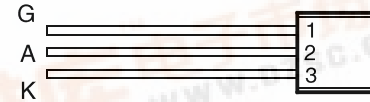


SC 2092 SERIES SILICON CONTROLLED RECTIFIERS

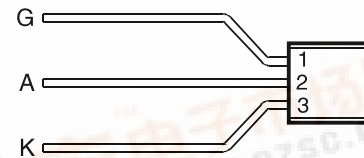
- 2 A Continuous On-State Current
- 15 A Surge-Current
- Glass Passivated Wafer
- 400 V to 600 V Off-State Voltage
- Max I_{GT} of 200 μA
- Package Options

PACKAGE	PACKING	PART # SUFFIX
LP	Bulk	(None)
LP with fomed leads	Tape and Reel	R

LP PACKAGE
(TOP VIEW)



LP PACKAGE
WITH FORMED LEADS
(TOP VIEW)



absolute maximum ratings **over operating case temperature (unless otherwise noted)**

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	SC2092-400-15	V_{DRM}	400	V
	SC2092-600-15		600	
Repetitive peak reverse voltage	SC2092-400-15	V_{RRM}	400	V
	SC2092-600-15		600	
Continuous on-state current at (or below) 85°C case temperature (see Note 2)		$I_{T(RMS)}$	2	A
Surge on-state current (see Note 3)		I_{TSM}	15	A
Peak positive gate current (pulse width $\leq 300 \mu s$)		I_{GM}	0.2	A
Average gate power dissipation (see Note 4)		$P_{G(AV)}$	0.3	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply when the gate-cathode resistance $R_{GK} = 1 k\Omega$.
2. These values apply for continuous dc operation with resistive load. Above 85°C derate linearly to zero at 110°C.
3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
4. This value applies for a maximum averaging time of 20 ms.

SC 20 SERIES

SILICON CONTROLLED RECTIFIERS

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{DRM}	Repetitive peak off-state current	$V_{\text{D}} = \text{rated } V_{\text{DRM}}$	$R_{\text{GK}} = 1 \text{ k}\Omega$			20	μA
I_{RRM}	Repetitive peak reverse current	$V_{\text{R}} = \text{rated } V_{\text{RRM}}$	$I_{\text{G}} = 0$			200	μA
I_{GT}	Gate trigger current	$V_{\text{AA}} = 6 \text{ V}$	$R_{\text{L}} = 100 \Omega$ $t_{\text{p(g)}} \geq 20 \mu\text{s}$		60	200	μA
V_{GT}	Gate trigger voltage	$V_{\text{AA}} = 6 \text{ V}$	$R_{\text{L}} = 100 \Omega$ $R_{\text{GK}} = 1 \text{ k}\Omega$ $t_{\text{p(g)}} \geq 20 \mu\text{s}$	0.4		1	V
I_{H}	Holding current	$V_{\text{AA}} = 6 \text{ V}$	$R_{\text{GK}} = 1 \text{ k}\Omega$ Initiating $I_{\text{T}} = 10 \text{ mA}$			5	mA
V_{TM}	Peak on-state voltage	$I_{\text{TM}} = 1 \text{ A}$	(see Note 5)			1.5	V

NOTE 5: This parameter must be measured using pulse techniques, $t_{\text{p}} = 1 \text{ ms}$, duty cycle $\leq 2 \%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

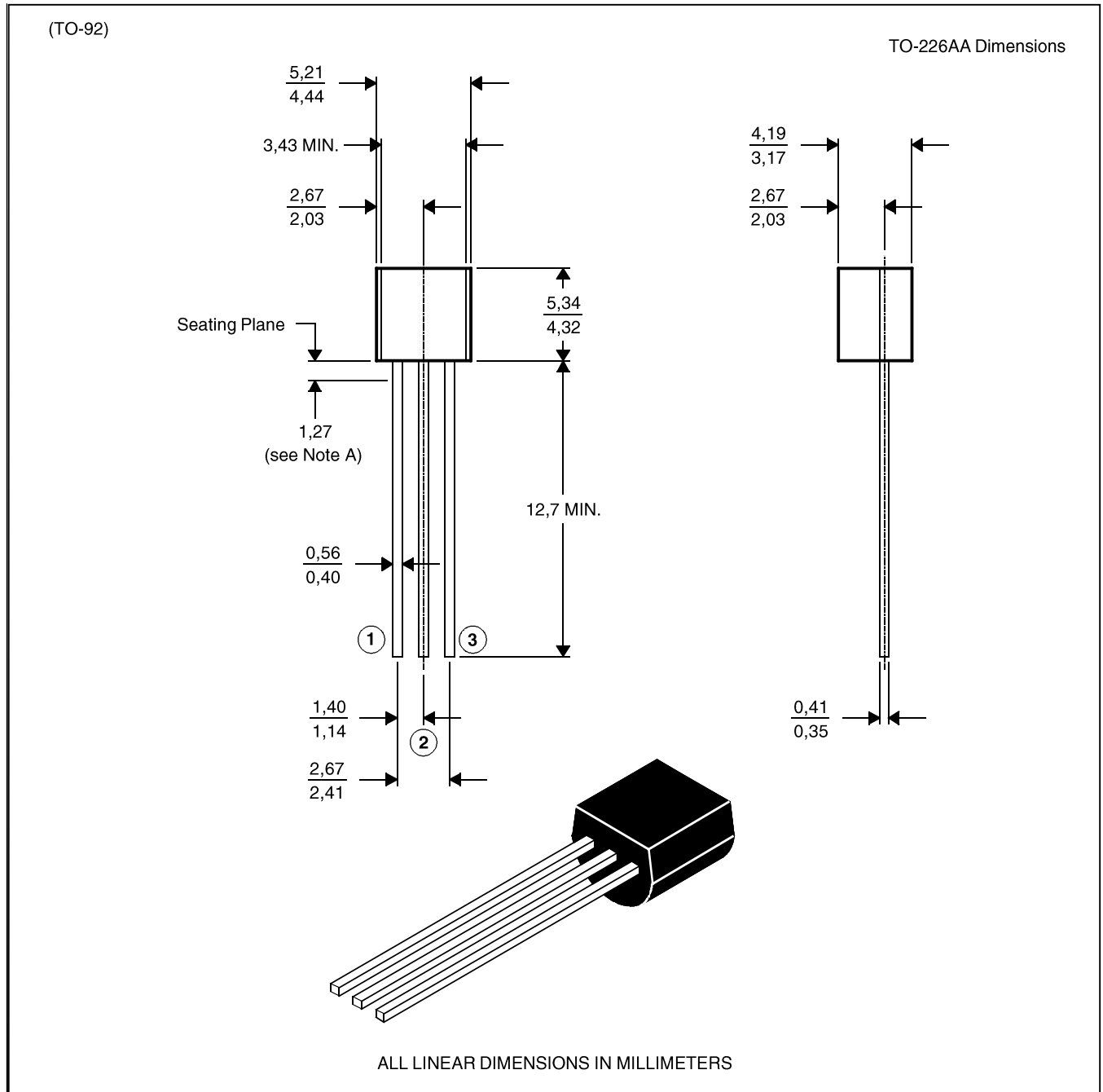
SC 20 SERIES SILICON CONTROLLED RECTIFIERS

MECHANICAL DATA

(TO-92)

3-pin cylindrical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



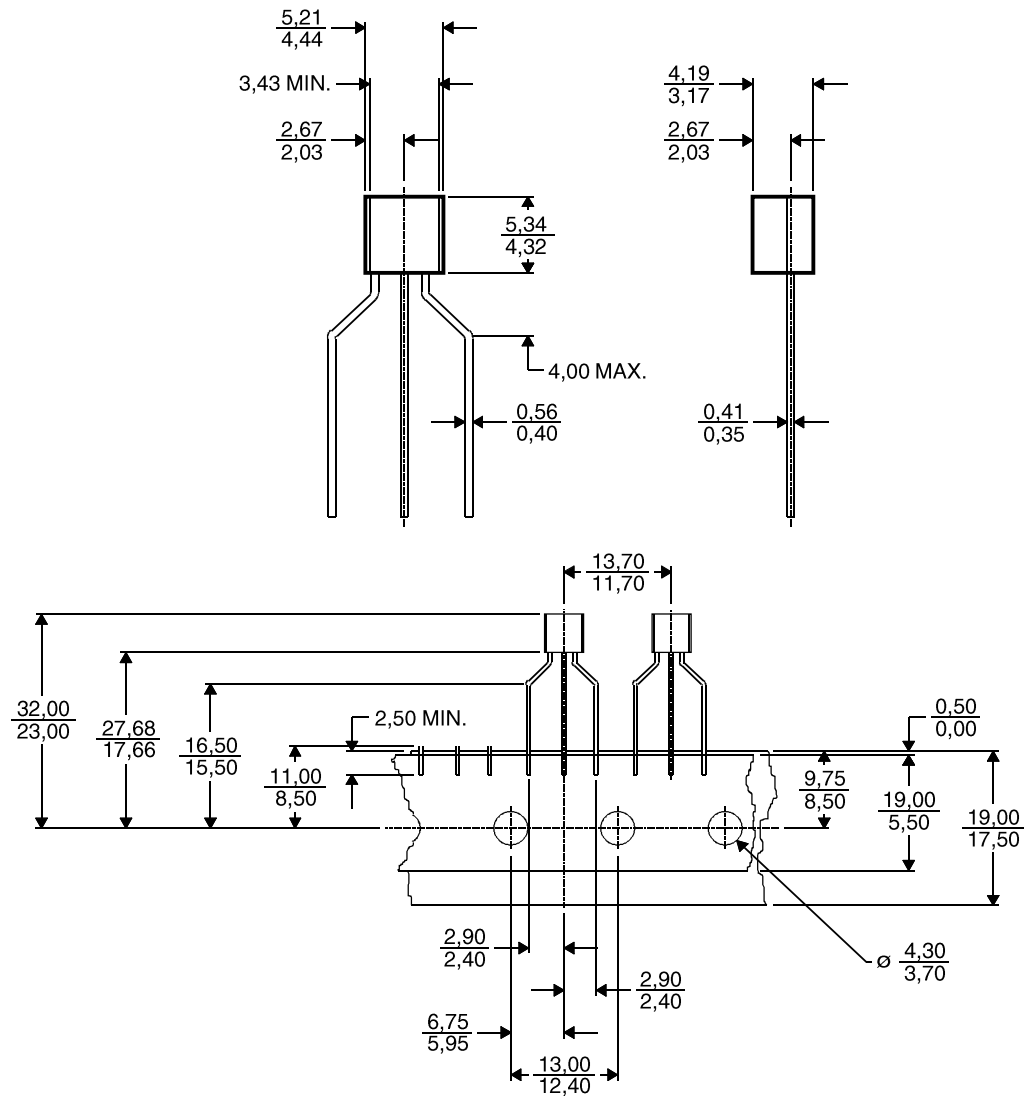
NOTE A: Lead dimensions are not controlled in this area.

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MECHANICAL DATA

tape dimensions

(TO-92) Tape (Formed Lead Version)



ALL LINEAR DIMENSIONS IN MILLIMETERS